

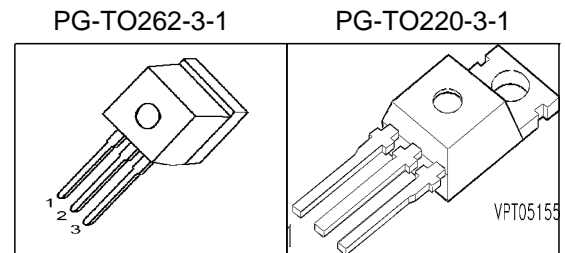
SIPMOS® Power-Transistor

Feature

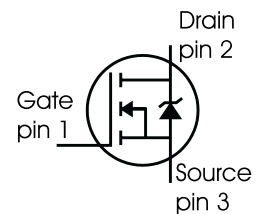
- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- dv/dt rated
- Pb-free lead plating; RoHS compliant

Product Summary

V_{DS}	100	V
$R_{DS(on)}$	14	mΩ
I_D	80	A



Type	Package	Ordering Code	Marking
SPP80N10L	PG-TO220-3-1	Q67042-S4173	80N10L
SPI80N10L	PG-TO262-3-1	Q67042-S4172	80N10L



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	80	A
$T_C=25\text{ °C}$		80	
$T_C=100\text{ °C}$		58	
Pulsed drain current	$I_{D\text{ puls}}$	320	
$T_C=25\text{ °C}$			
Avalanche energy, single pulse	E_{AS}	700	mJ
$I_D=80\text{ A}$, $V_{DD}=25\text{ V}$, $R_{GS}=25\text{ Ω}$			
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	25	
Reverse diode dv/dt	dv/dt	6	kV/μs
$I_S=80\text{ A}$, $V_{DS}=0\text{ V}$, $di/dt=200\text{ A/μs}$			
Gate source voltage	V_{GS}	±20	V
Power dissipation	P_{tot}	250	W
$T_C=25\text{ °C}$			
Operating and storage temperature	T_j, T_{stg}	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

